

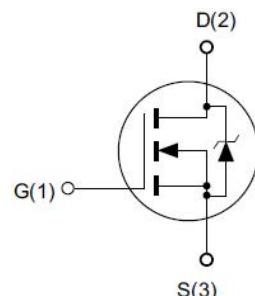
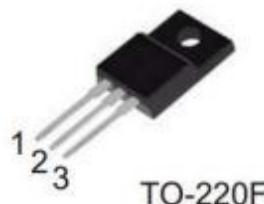


# MPF03NA5

## N-Channel Power MOSFET

### Features

- ◆ 1500V, 3A,  $R_{DS(ON)}$ (Typ.) = 5Ω@VGS = 10V.
- ◆ Low ON Resistance
- ◆ Fast Switching
- ◆ Low Gate Charge
- ◆ 100% Single Pulse avalanche energy Test



### Application

- ◆ Power switch circuit of adaptor and charger

**Absolute Maximum Ratings**  $T_c = 25^\circ C$  unless otherwise noted

| Symbol         | Parameter                                      | Limit      | Unit |
|----------------|--|------------|------|
| $V_{DS}$       | Drain-Source Voltage <sup>a</sup>              | 1500       | V    |
| $V_{GS}$       | Gate-Source Voltage                            | $\pm 30$   | V    |
| $I_D$          | Drain Current-Continuous, $T_c = 25^\circ C$   | 3          | A    |
|                | Drain Current-Continuous, $T_c = 100^\circ C$  | 1.8        | A    |
| $I_{DM}$       | Drain Current-Pulsed <sup>b</sup>              | 12         | A    |
| $P_D$          | Maximum Power Dissipation @ $T_j = 25^\circ C$ | 32         | W    |
| EAS            | Single Pulsed Avalanche Energy <sup>d</sup>    | 245        | mJ   |
| $T_j, T_{STG}$ | Operating and Store Temperature Range          | -55 to 150 | °C   |

### Thermal Characteristics

| Symbol          | Parameter                                | Value | Unit |
|-----------------|--|-------|------|
| $R_{\theta JC}$ | Thermal Resistance, Junction-Case Max.   | 3.8   | °C/W |
| $R_{\theta JA}$ | Thermal Resistance Junction-Ambient Max. | 62.5  | °C/W |

**Electrical Characteristics**  $T_j = 25^\circ C$  unless otherwise noted

### Off Characteristics

| Symbol     | Parameter                         | Test Condition                    | Min. | Typ. | Max.      | Unit |
|------------|-----------------------------------|-----------------------------------|------|------|-----------|------|
| $BV_{DSS}$ | Drain-Source Breakdown Voltage    | $V_{GS} = 0V, I_D = 250\mu A$     | 1500 | -    | -         | V    |
| $I_{DSS}$  | Zero Gate Voltage Drain Current   | $V_{DS} = 1500V$<br>$V_{GS} = 0V$ | -    | -    | 25        | μA   |
| $I_{GSS}$  | Forward Gate Body Leakage Current | $V_{DS} = 0V, V_{GS} = \pm 30V$   | -    | -    | $\pm 100$ | nA   |



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### On Characteristics

| Symbol       | Parameter                                      | Test Condition                       | Min. | Typ. | Max. | Unit     |
|--------------|--|--------------------------------------|------|------|------|----------|
| $V_{GS(th)}$ | Gate Threshold Voltage                         | $V_{DS} = V_{GS}$ , $I_D = 250\mu A$ | 3    | -    | 5    | V        |
| $R_{DS(on)}$ | Static Drain-Source On-Resistance <sup>c</sup> | $V_{GS} = 10V$ , $I_D = 1.5A$        | -    | 5.0  | 6.5  | $\Omega$ |

### Dynamic Characteristics

| Symbol    | Parameter                    | Test Condition                                      | Min. | Typ. | Max. | Unit |
|-----------|------------------------------|---|------|------|------|------|
| $C_{iss}$ | Input Capacitance            | $V_{DS} = 25V$ ,<br>$V_{GS} = 0V$ ,<br>$f = 1.0MHz$ | -    | 2036 | -    | pF   |
| $C_{oss}$ | Output Capacitance           |   | -    | 98   | -    | pF   |
| $C_{rss}$ | Reverse Transfer Capacitance |   | -    | 12.8 | -    | pF   |

### On Characteristics

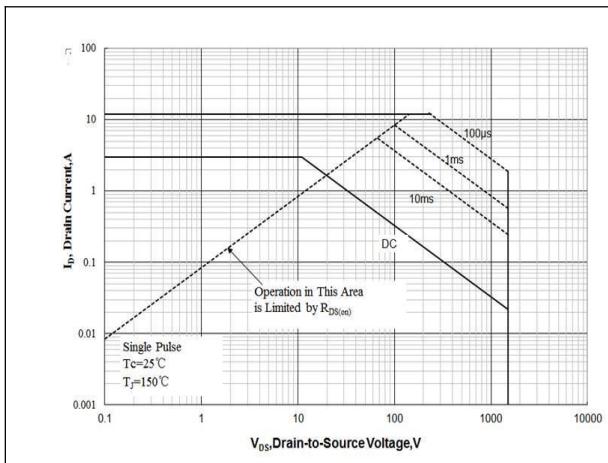
| Symbol       | Parameter           | Test Condition                                       | Min. | Typ. | Max. | Unit |
|--------------|---------------------|--|------|------|------|------|
| $t_{d(on)}$  | Turn-On Delay Time  | $V_{DD} = 750V$ , $I_D = 3A$ ,<br>$R_G = 10\Omega$ , | -    | 35.8 | -    | ns   |
| $t_r$        | Turn-On Rise Time   |  | -    | 19.4 | -    | ns   |
| $t_{d(off)}$ | Turn-Off Delay Time |  | -    | 56   | -    | ns   |
| $t_f$        | Turn-Off Fall Time  |  | -    | 31.2 | -    | ns   |
| $Q_g$        | Total Gate Charge   | $V_{DD} = 750V$ , $I_D = 3A$ ,<br>$V_{GS} = 10V$     | -    | 37.6 | -    | nC   |
| $Q_{gs}$     | Gate-Source Charge  |  | -    | 9.9  | -    | nC   |
| $Q_{gd}$     | Gate-Drain Charge   |  | -    | 14.4 | -    | nC   |

### Drain-Source Diode Characteristics

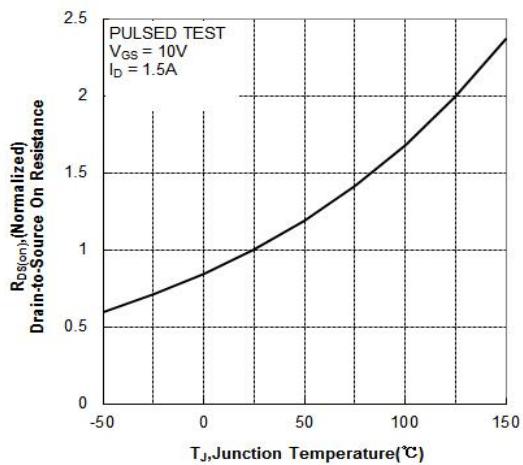
| Symbol   | Parameter                                     | Test Condition  | Min. | Typ. | Max. | Unit |
|----------|---|---|------|------|------|------|
| $I_s$    | Drain-Source Diode Forward Continuous Current | $V_{GS} = 0V$   | -    | -    | 3    | A    |
| $I_{SM}$ | Maximum Pulsed Current                        | $V_{GS} = 0V$   | -    | -    | 12   | A    |
| $V_{SD}$ | Drain-Source Diode Forward Voltage            | $V_{GS} = 0V$ , $I_s = 3A$  | -    | -    | 1.5  | V    |
| $trr$    | Reverse Recovery Time                         | $I_s=3A$ , $T_j = 25^\circ C$<br>$dI/dt=100A/us$ ,<br>$V_{GS}=0V$ | -    | 882  | -    | ns   |
| $Qrr$    | Reverse Recovery Charge                       |   | -    | 6.5  | -    | uC   |

Notes:

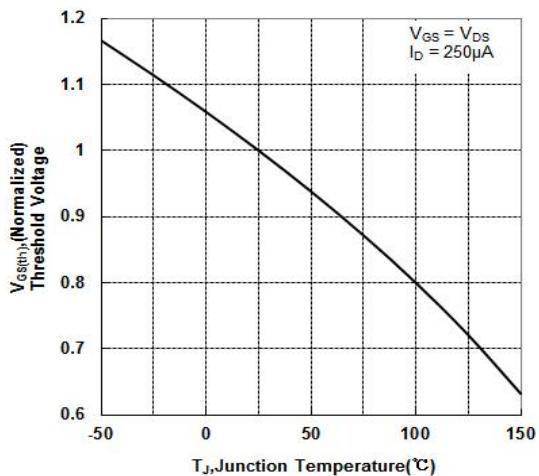
- a.  $T_J = +25^\circ C$  to  $+150^\circ C$
- b. Repetitive rating; pulse width limited by maximum junction temperature.
- c. Pulse width  $\leq 300\mu s$ ; duty cycle  $\leq 2\%$
- d.  $L=10mH$ ,  $V_{DD}=50V$ ,  $I_{as}=7A$ ,  $R_G=25\Omega$  Starting  $T_J=25^\circ C$



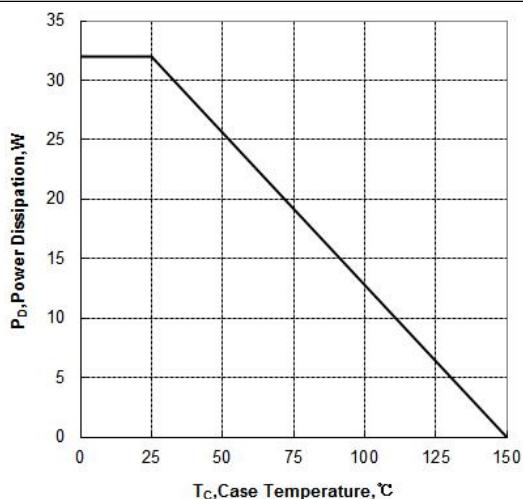
**Figure 1. Maximum Safe Operating Area**



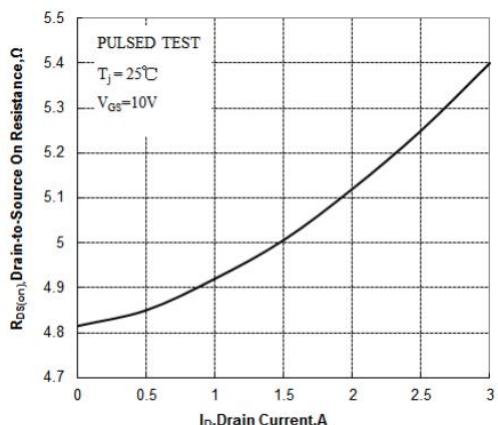
**Figure 2. Normalized On-Resistance Variation with Temperature**



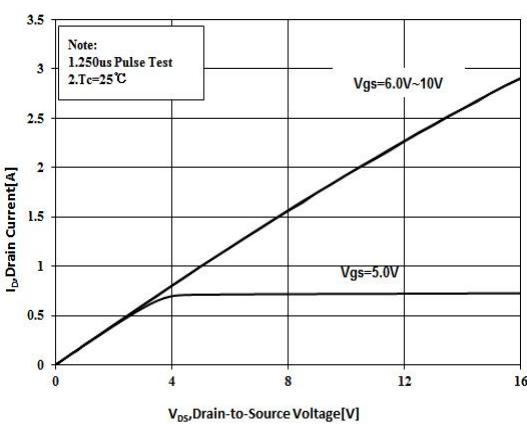
**Figure 3. Gate Threshold Variation with Temperature**



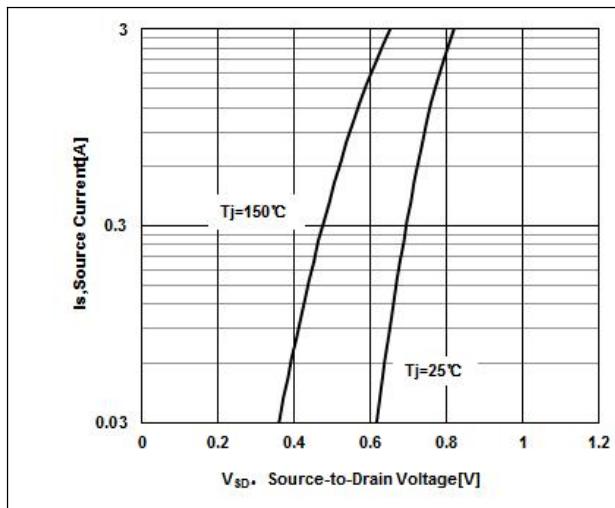
**Figure 4. Maximum Drain Current with Case Temperature**



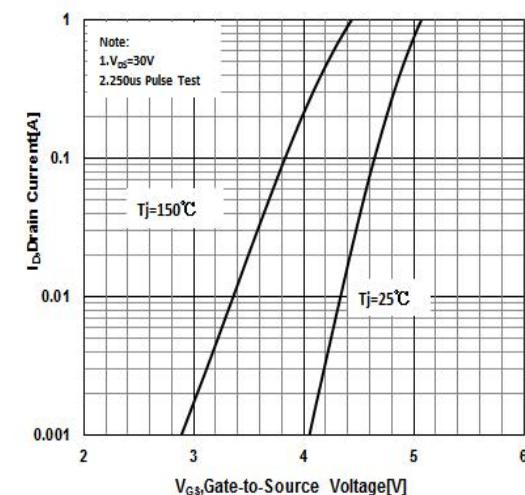
**Figure 5. Typical Drain to Source ON Resistance vs Drain Current**



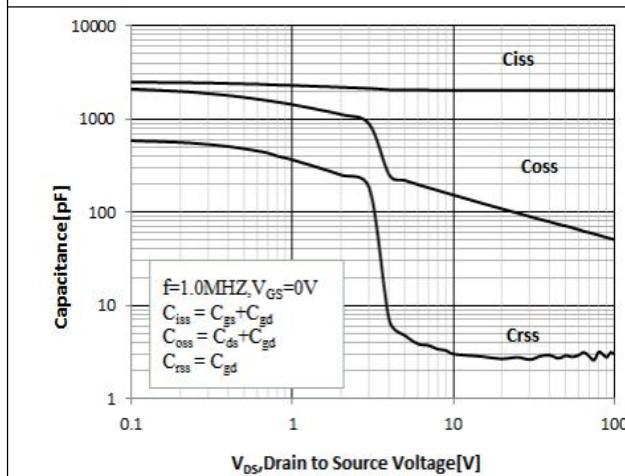
**Figure 6. On-State Characteristics**



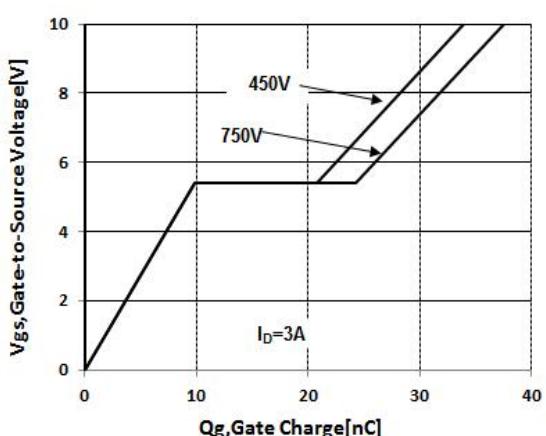
**Figure 7. Body Diode Forward Voltage Variation with Source Current**



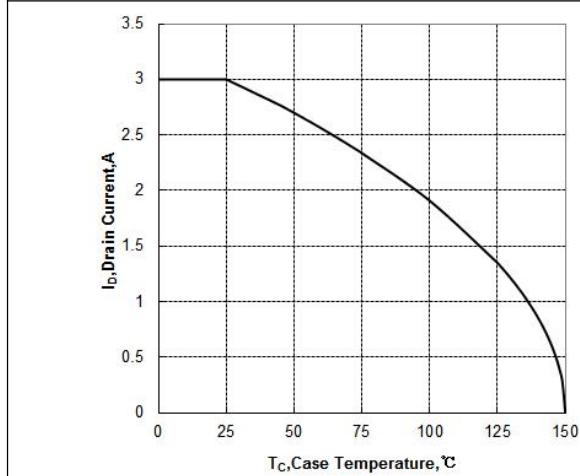
**Figure 8. Transfer Characteristics Variation with Source Current**



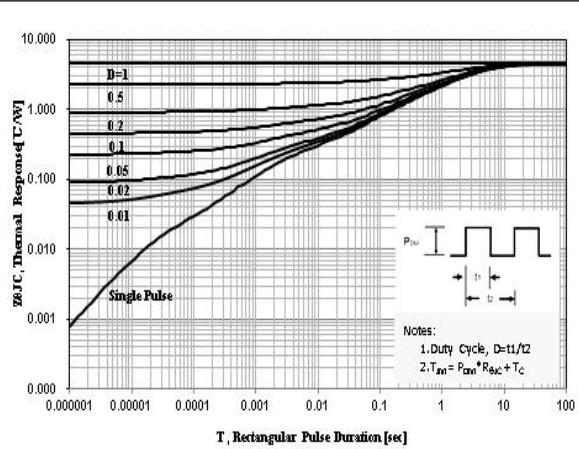
**Figure 9. Capacitance Characteristics**



**Figure 10. Gate Charge Characteristics**



**Figure 11. Maximum Continuous Drain VS Case Temperature**



**Figure 12. Normalized Effective Transient Thermal Impedance With Pulse Duration**

## ■ Package Information

